

(Use several sheets if necessary)

Agitation Number

10/756, 568

Seiki Ogura et al.

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Group 27 Unit

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TL	-	Chang et al., "A New Sense Memory Using Source-Side Injection for Programming," IEEE Electron Device Letters, Vol. 19, No. 7, pp. 253-255, July 1998.
TL	-	Ogura et al., "Low Voltage, Low Current, High Speed Program Step Split Gate Cell with Ballistic Direct Injection for EEPROM/Flash," TEDM 1998, p. 987

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.